

Micro-power PT3666 Hi-Sensitivity Hall-effect Switch

Applications

- · Cover detector
- · Battery-operated
- Hand Held Equipment

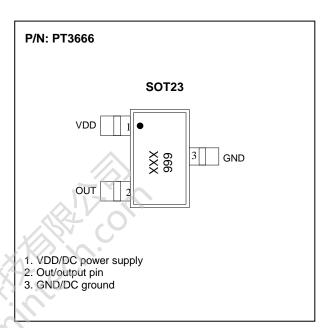
Features

- 2.4V to 5.5V operation range
- · Built-in dynamic offset cancellation
- Small size
- · High balance and low thermal drift magnetic sensing
- Micro power Operation
- ESD protected to 5KV(HBM)

Order information

PT3666 /PKG:SOT23

Package Type



Specifications

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Conditions	Rating	Units
Maximum supply voltage	V _{DD} max		7	V
Allowable power dissipation	Pd	SOT23	300*	mW
Operating temperature	Та		-40~+85	$^{\circ}\!\mathbb{C}$
Storage temperature	Ts		-55~+150	$^{\circ}\!\mathbb{C}$
Max. output current	I _{OMAX}		5	mA

^{*:} On 50mm x 50mm x 1.6mm glass epoxy board

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General Specifications

The PT3666 is designed for battery-operated, hand-held equipment such as cellular and cordless phone, PDA and pagers application. The built-in dynamic offset cancellation of pre-amplifier stage achieves optimal symmetrical magnetic sensing.

This Hall effect sensor IC integrate a sensor, pre-amplifier with dynamic offset cancellation and the differential hysteresis comparator in single chip. The architecture block diagram is shown in Fig. 1.

The micro power operation is achieved by the awake/sleep timing control as shown Fig2. The chip will be automatic at awake mode for 40uS and is at sleep mode (shutdown) for the remainder of the period (40mS). At awake mode, the sensor of chip will be enable and normal operation. The sensor will be disabled to save the power and the output is latched in the previous state during sleep mode.

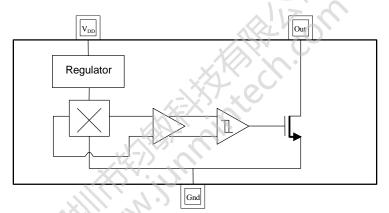


Fig. 1. Functional diagram

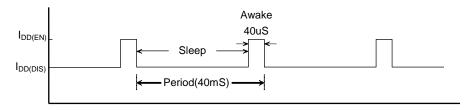


Fig 2. Awake/Sleep timing

Ver 1.0 -2- Date: Oct-2014



Electrical Characteristics (T_A=+25°C, V_{DD}=2.75V)

	•	•	•			
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Units
Supply Voltage	V_{DD}	Operating	2.4	-	5.5	V
Output Sink Voltage	V _{DS(ON)}	I _{OUT} =1mA, V _{DD} =2.75V	-	0.1	0.25	V
Supply Current	I _{AWK}	Awake, V _{DD} =2.75V	-	3	5	mA
	I _{SLP}	Sleep, V _{DD} =2.75V	-	2	4	μΑ
	I _{AVG}	V _{DD} =2.75V	-	4	10	μΑ
Awake Time	T _{AWK}	Operating	-	40	90	μS
Period	T _P	Operating	-	40	70	mS
Duty Cycle			-	0.1	-	%

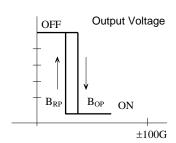
Magnetic Characteristics (T_A=+25°C, V_{DD}=2.75V)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Units
Operate Point	B _{OP}	South operate point	7-0	±35	±70	G
Release Point	B _{RP}	South release point	±10	±35	-	G
Hysteresis	B _{HYS}	B _{OPX} - B _{RPX}	, ,	10		G

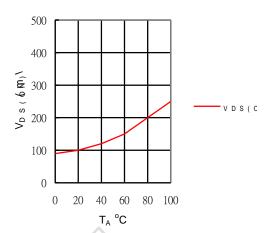




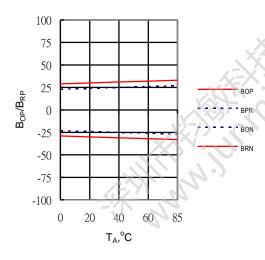
Magnetic Flux Density in Gauss



Output sink voltage ve

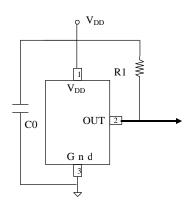


 $B_{\text{OP}},\,B_{\text{RP}}$ versus temperature



PT3666 Hall IC

Application circuits



NOTE:

C0: 0.1uF decoupling capacitor R1: >470Kohm is recommended

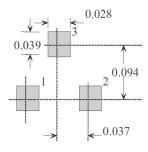
Ordering information

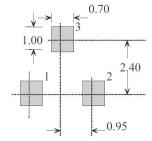
Part NO.	Marking NO.	Package	Temperature
PT3666	666	SOT-23	-40~85C Extended

Solder-Pad Layout

Dimensions in Inches

Dimensions in millimeters

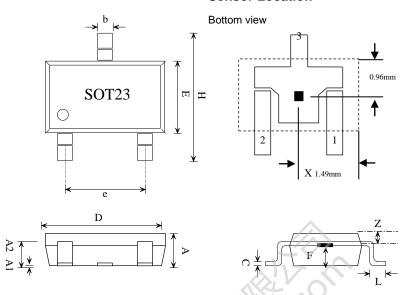






Package Outline

Sensor Location



CYMPOLC	DIMENSIONS IN MILLIMETERS(mm)					
SYMBOLS	MIN	NOM	MAX			
A	1.00	1.10	1.30			
A1	0.00	-	0.10			
A2	0.70	0.80	0.90			
-6	0.35	0.40	0.50			
C	0.10	0.15	0.25			
D	2.70	2.90	3.10			
Е	1.40	1.80	2.00			
F	0.35	0.50	0.65			
Н	2.60	2.8	3.00			
e	1.7	1.9	2.1			
L	0.20	-	-			
SENSOR LOCATION						
X	-	0.96	-			
Y	-	1.49	-			
Z	-	0.50	-			